

N- and P-Channel 30-V (D-S) MOSFET

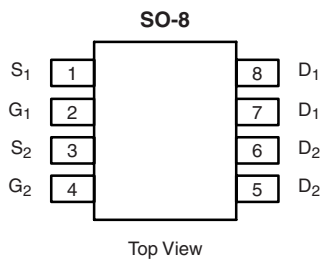
PRODUCT SUMMARY			
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
N-Channel	30	0.053 at V _{GS} = 10 V	4.9
		0.075 at V _{GS} = 4.5 V	4.1
P-Channel	- 30	0.080 at V _{GS} = - 10 V	- 3.9
		0.135 at V _{GS} = - 4.5 V	- 3.0

FEATURES

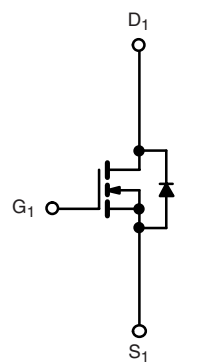
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs



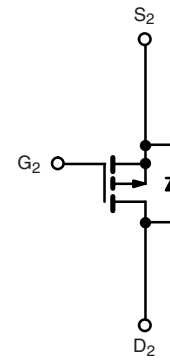
RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si4532ADY-T1-E3 (Lead (Pb-free)
Si4532ADY-T1-GE3 (Lead (Pb-free and Halogen-free)



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		10 s	Steady State	10 s	Steady State		
Drain-Source Voltage	V _{DS}	30		- 30		V	
Gate-Source Voltage	V _{GS}	± 20		± 20			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	4.9	3.7	- 3.9	- 3.0	A
		T _A = 70 °C	3.9	2.9	- 3.1	- 2.4	
Pulsed Drain Current	I _{DM}	20					
Continuous Source Current (Diode Conduction) ^a	I _S	1.7	0.94	- 1.7	- 1.0		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2	1.13	2	1.2	W
		T _A = 70 °C	1.3	0.73	1.3	0.76	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	55	62.5	54	62.5	°C/W
	Steady State		90	110	87	105	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	50	34	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

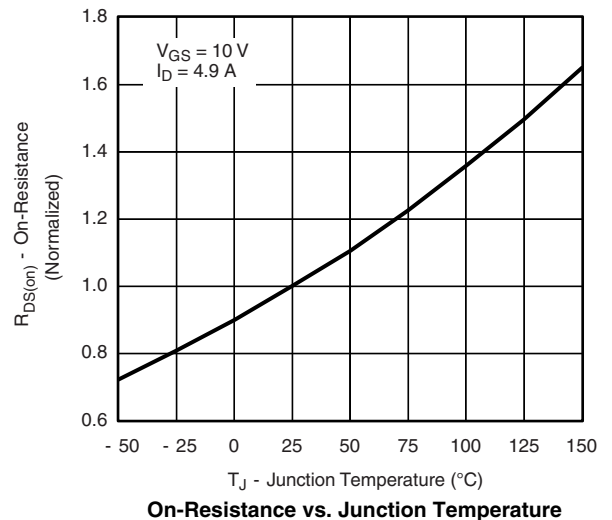
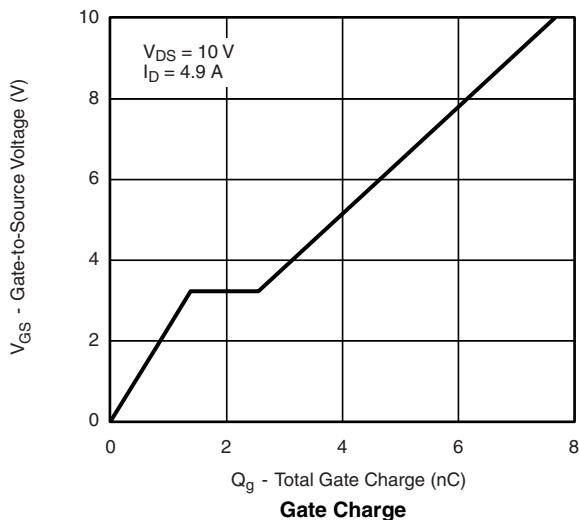
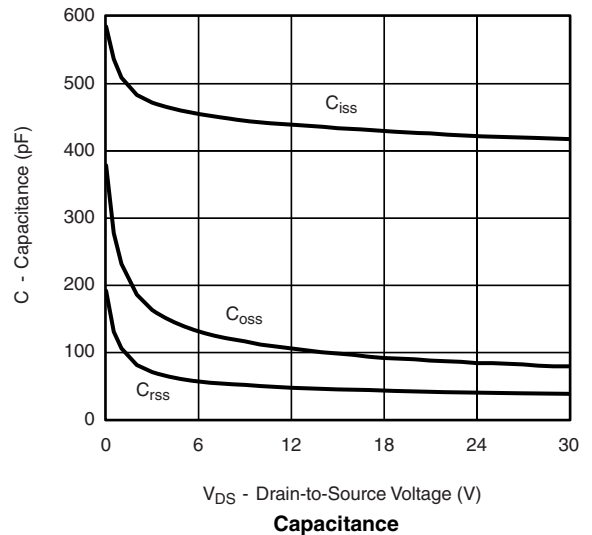
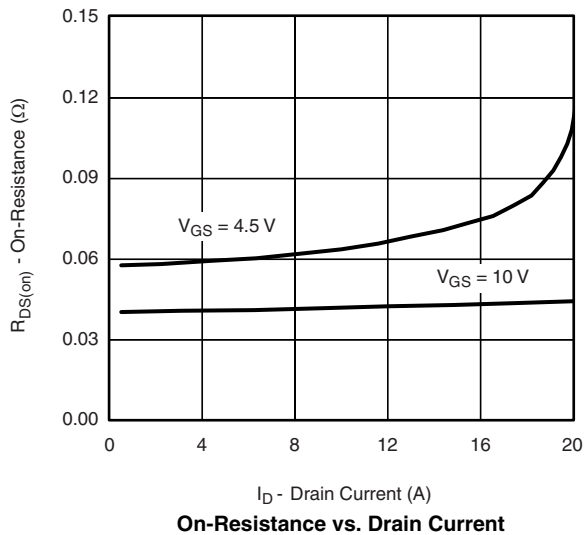
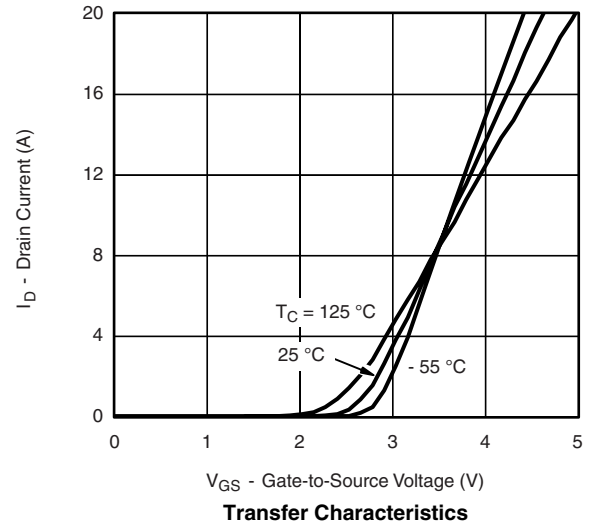
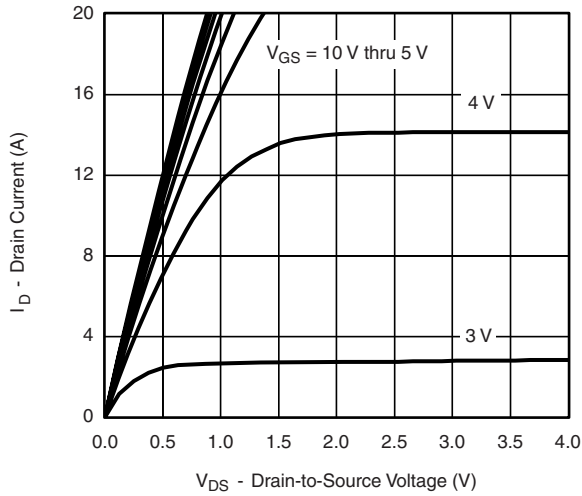
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	1.0			V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-1.0			
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch			± 100	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	P-Ch			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			5	
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	20			A
		$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	P-Ch	-20			
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 4.9\text{ A}$	N-Ch		0.044	0.053	Ω
		$V_{GS} = -10\text{ V}, I_D = -3.9\text{ A}$	P-Ch		0.062	0.080	
		$V_{GS} = 4.5\text{ V}, I_D = 4.1\text{ A}$	N-Ch		0.062	0.075	
		$V_{GS} = -4.5\text{ V}, I_D = -3.0\text{ A}$	P-Ch		0.105	0.135	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 4.9\text{ A}$	N-Ch		11		S
		$V_{DS} = -15\text{ V}, I_D = -2.5\text{ A}$	P-Ch		5		
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.80	1.2	V
		$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$	P-Ch		-0.82	-1.2	
Dynamic^b							
Total Gate Charge	Q_g	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 4.9\text{ A}$	N-Ch		8	16	nC
Gate-Source Charge	Q_{gs}		P-Ch		10	20	
Gate-Drain Charge	Q_{gd}	P-Channel $V_{DS} = -4\text{ V}, V_{GS} = -10\text{ V}, I_D = -3.9\text{ A}$	N-Ch		1.4		nC
			P-Ch		2		
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		12	20	ns
			P-Ch		8	15	
Rise Time	t_r	P-Channel $V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		10	20	ns
			P-Ch		9	18	
Turn-Off Delay Time	$t_{d(off)}$	N-Channel $V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		23	45	ns
			P-Ch		21	40	
Fall Time	t_f	P-Channel $V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$	N-Ch		8	15	ns
			P-Ch		10	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$	N-Ch		25	40	ns
		$I_F = -1.7\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}$	P-Ch		27	40	

Notes:

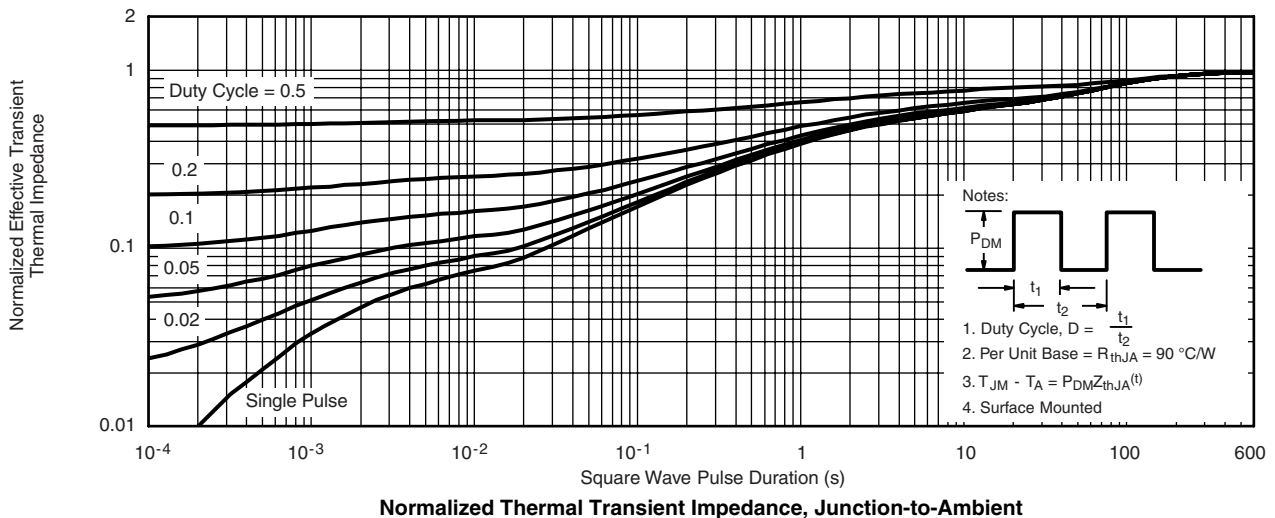
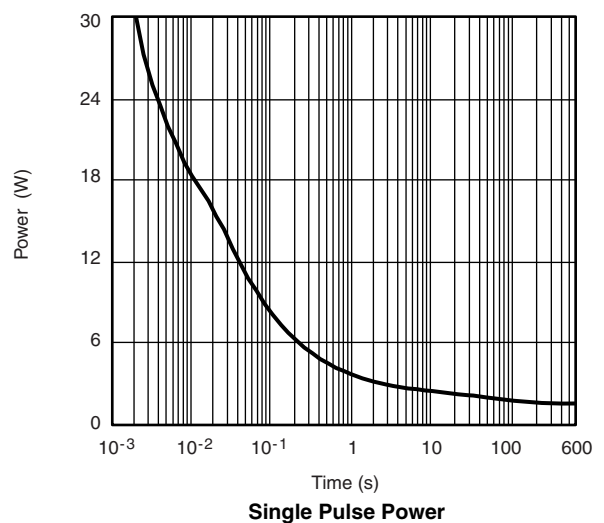
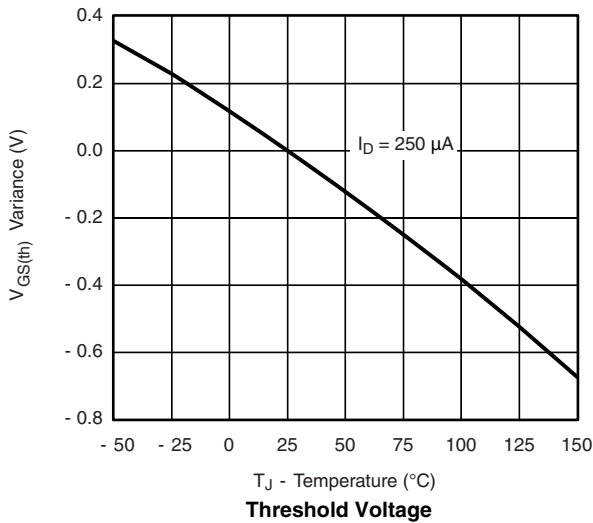
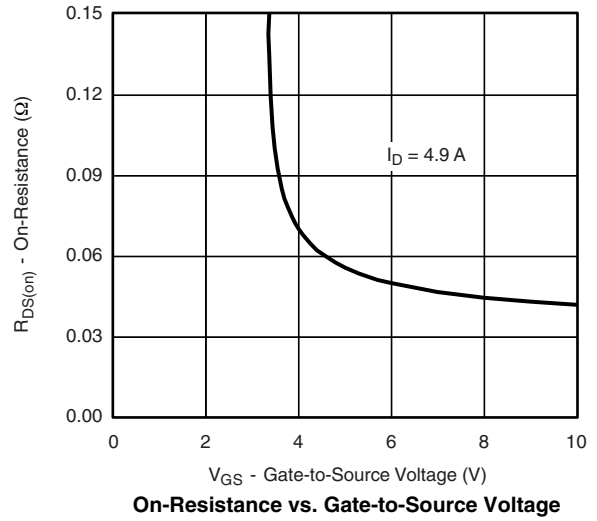
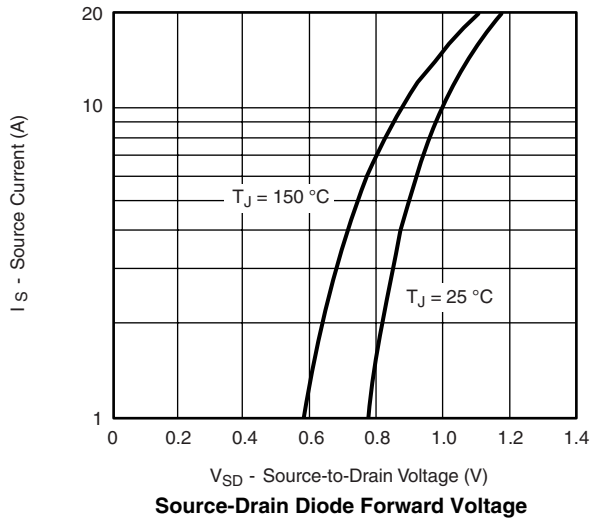
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

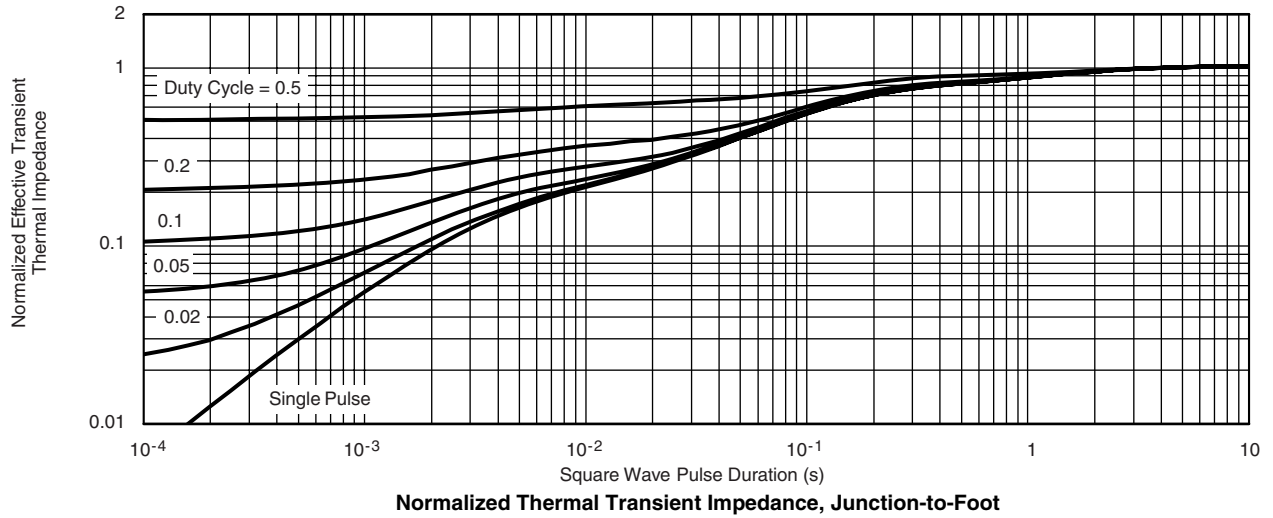
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



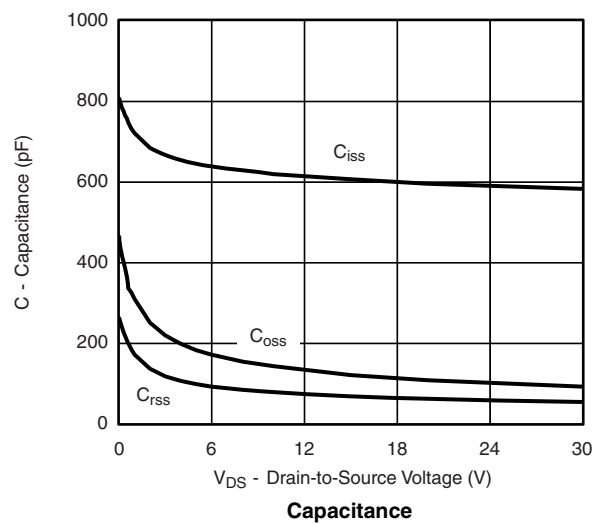
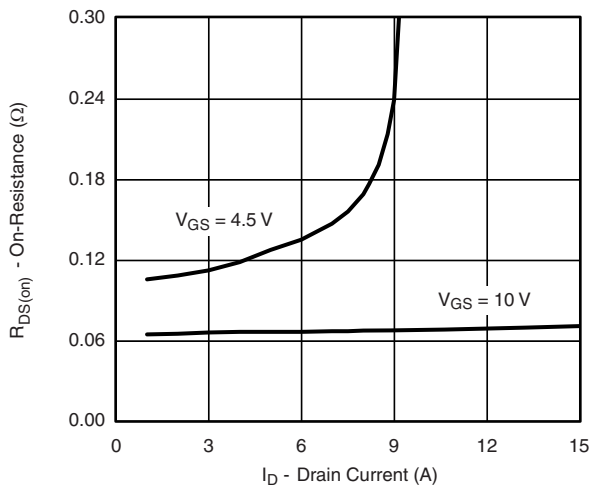
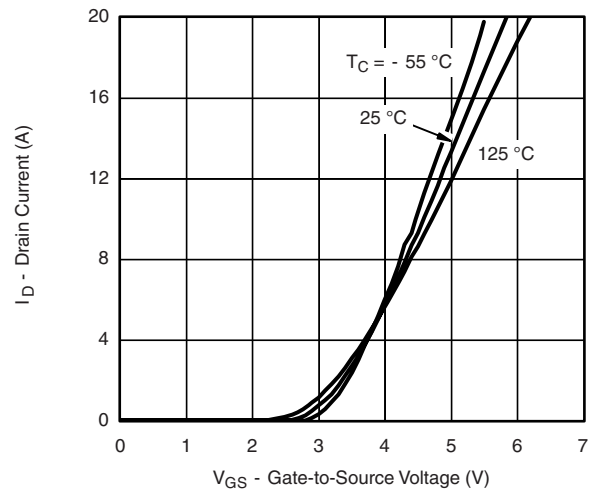
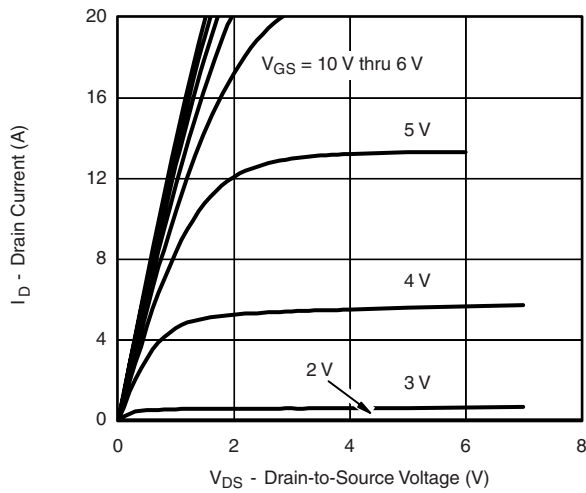
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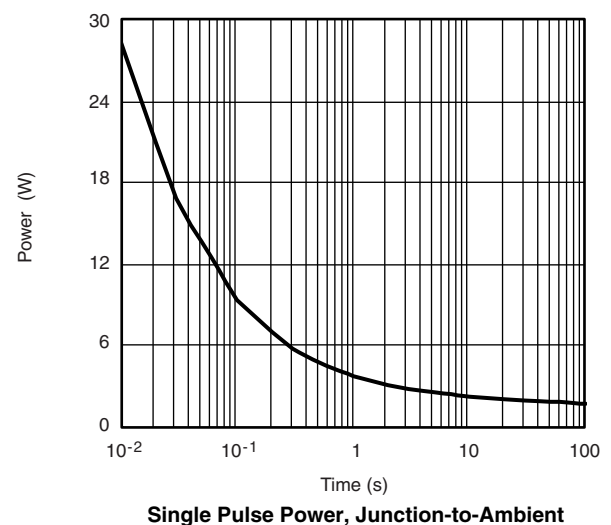
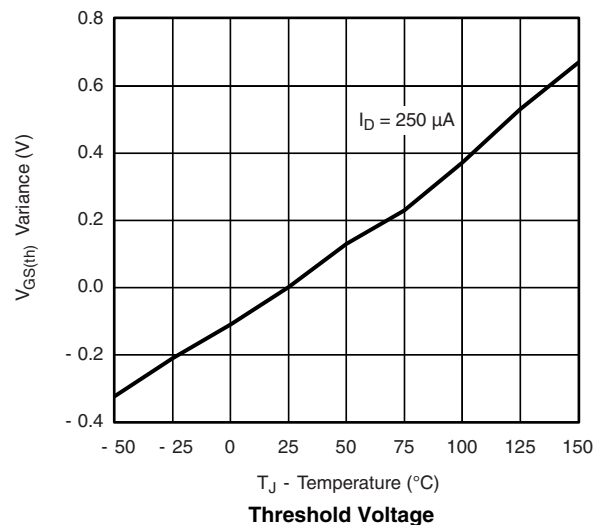
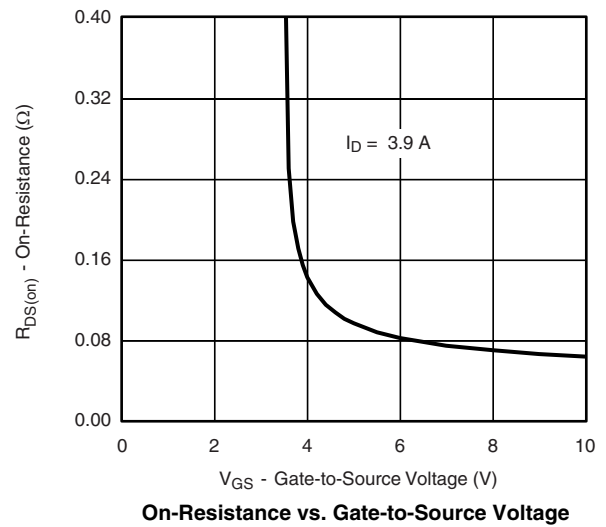
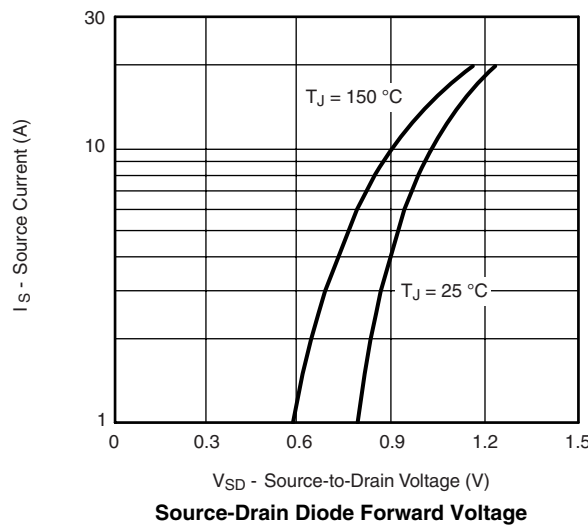
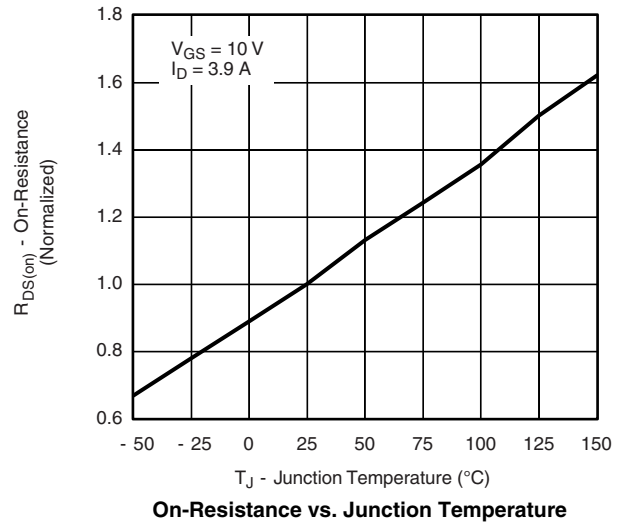
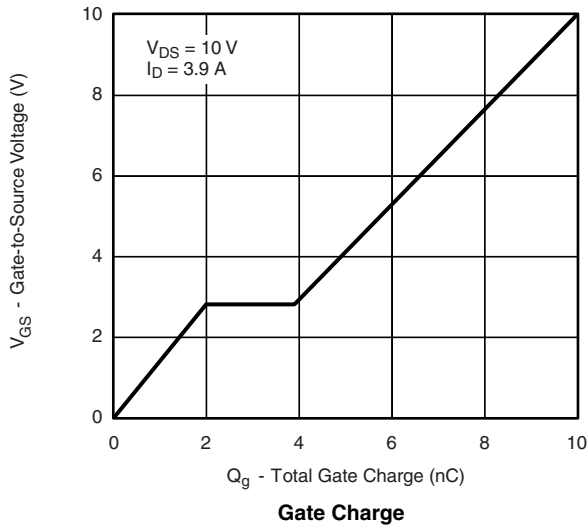
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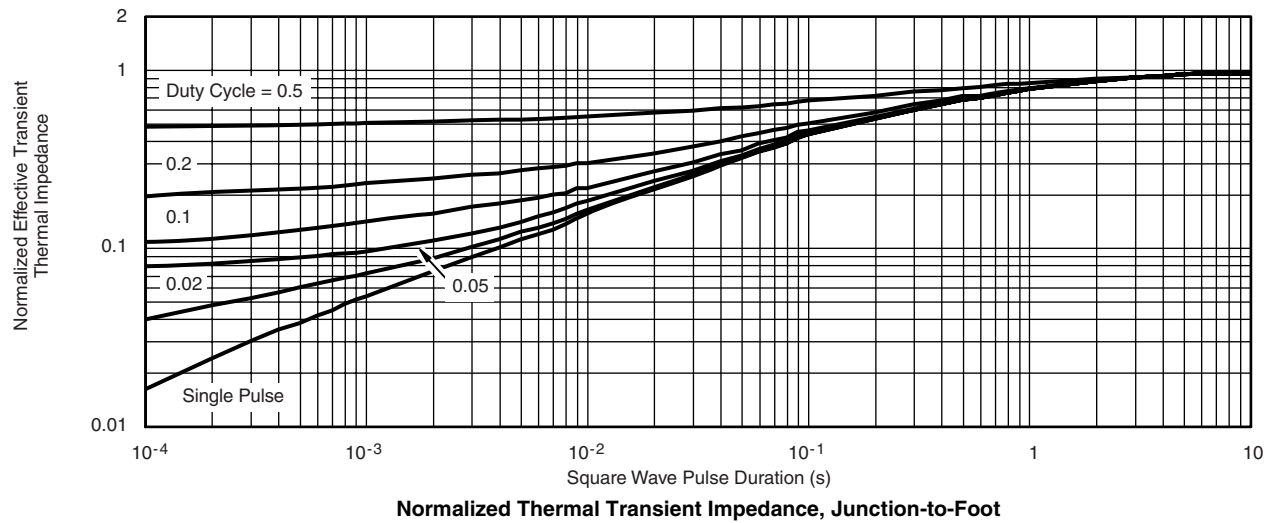
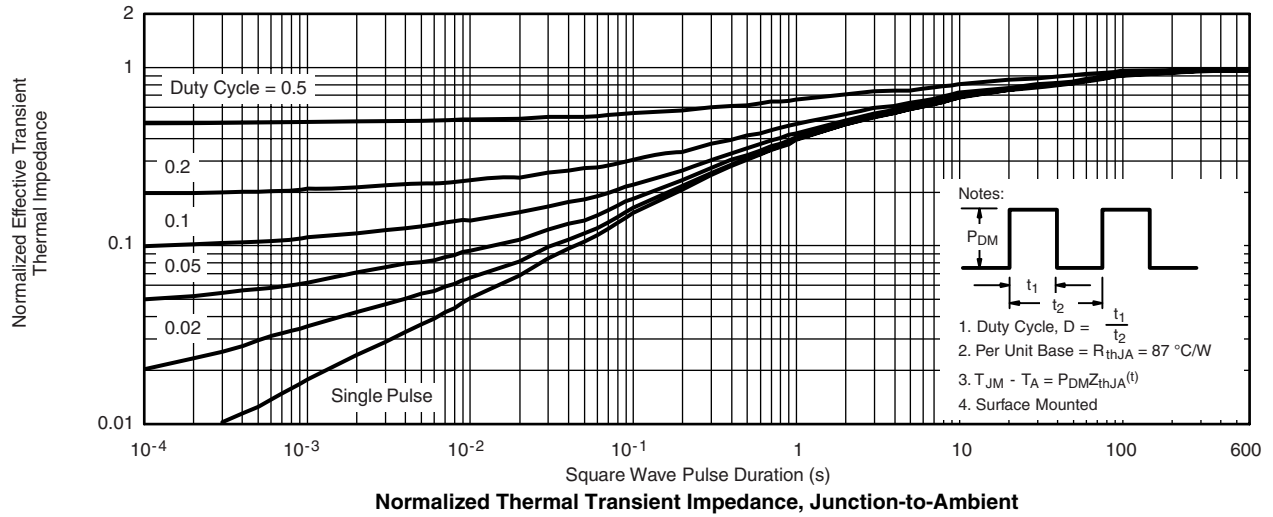
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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